## IN THE CLAIMS:

The following is a complete listing of the claims, reflects all changes currently being made thereto, and replaces all earlier versions and listings:

- (currently amended): An electron-emitting device comprising:
   a cathode electrode;
   a layer electrically connected to the cathode electrode; and
   a plurality of particles, each comprising as a main component a material
   which has resistivity lower than resistivity of a material of the layer, wherein
- which has resistivity lower than resistivity of a material of the layer, wherein the plurality of particles are arranged in the layer[[;]], and a density of the particles in the layer is  $1 \times 10^{14}$ /cm<sup>3</sup> or more and  $5 \times 10^{18}$ /cm<sup>3</sup> or less.
  - (currently amended): An electron-emitting device comprising: a cathode electrode:
  - a layer electrically connected to the cathode electrode; and a plurality of particles, each comprising as a main component a material,
- which has resistivity lower than resistivity of a material of the layer, wherein[[,]]
  the plurality of particles are arranged in the layer[[;]], and
  a concentration of a main element of the particles with respect to a main
- a concentration of a main element of the particles with respect to a selement of the layer is 0.001 atm% or more and 1.5 atm% or less.

a cathode electrode:

- 3. (currently amended): An electron-emitting device comprising:
- a layer electrically connected to the cathode electrode; and

a plurality of particles, each comprising as a main component a material which has resistivity lower than resistivity of a material of the layer, wherein

the plurality of particles are arranged in the layer[[;]],

a density of the particles in the layer is  $1\times10^{14}/cm^3$  or more and  $5\times10^{18}/cm^3$  or less[[;1], and

a concentration of a main element of the particles with respect to a main element of the layer is 0.001 atm% or more and 1.5 atm% or less.

- 4. (currently amended): An electron-emitting device comprising:
- a cathode electrode;
- a layer which is arranged on the cathode layer and contains carbon as a main component; and

at least two particles which are arranged so as to be adjacent to each other in the laver and comprises metal as a main component, wherein

one of the adjacent two particles is arranged to be nearer to the cathode electrode than the other particle[[;]], and

the metal is [[metal]] selected from the group consisting of Co, Ni, and Fe.

- 5. (currently amended): An electron-emitting device comprising:
- a cathode electrode; and
- a layer connected to the cathode electrode, wherein
- a plurality of groups of particles, each group being constituted by at least two particles adjacent to each other, are arranged in the layer[[;]].

each of the particles comprises as a main component a material which has resistivity lower than resistivity of a material of the layer,

the adjacent two particles are arranged in a range of 5 nm or less[[:]], one of the adjacent two particles is arranged to be nearer to the cathode electrode than the other particle[[:]], and

the plurality of groups of particles are arranged apart from each other by <u>a</u> <u>distance equal to</u> an average film thickness of the layer or more.

- 6. (currently amended): An electron-emitting device comprising:
- a cathode electrode; and
- a layer connected to the cathode electrode, wherein
- a plurality of groups of particles, each group being constituted by at least two particles which comprise metal as a main component and are adjacent to each other, are arranged in the layer[[:]].

the layer comprises as a main component a material which has resistivity higher than resistivity of the particles [[:]].

the adjacent two particles are arranged in a range of 5 nm or less[[:]], and one of the adjacent two particles is arranged to be nearer to the cathode electrode than the other particle.

- 7. (currently amended): An electron-emitting device comprising:
- a cathode electrode; and
- a layer which is connected to the cathode electrode and comprises carbon as a main component, wherein
- a plurality of groups of particles, each group being constituted by at least two particles which comprise metal as a main component and are adjacent to each other, are arranged in the layer[[:]].

the plurality of groups of particles are arranged apart from each other by a distance equal to an average film thickness of the layer or more[[;]], and

a concentration of the metal in the carbon layer is lower on a surface side of the carbon layer than on the cathode electrode side.

- 8. (currently amended): An electron-emitting device comprising:
- a cathode electrode; and
- a layer which is connected to the cathode electrode and comprises carbon as a main component, wherein
- a plurality of groups of particles constituted by at least two particles, which comprise metal as a main component, being adjacent to each other are arranged in the layer,

one of the adjacent two particles is arranged on the cathode electrode than the other particle  $[[:]]_{a}$  and

 $\label{eq:graphene} graphene\ is\ included\ between\ adjacent\ particles\ among\ at\ least\ part\ of\ the$  plurality of particles.

- 9. (original): An electron-emitting device comprising:
- a cathode electrode:
- a layer which is electrically connected to the cathode electrode and comprises carbon as a main component; and
- a plurality of conductive particles arranged in the layer, each particle comprising carbon as a main component, wherein
- the layer comprising carbon as a main component contains a hydrogen element of 0.1 atm% or more with respect to a carbon element.

- 10. (original): An electron-emitting device according to claim 9, wherein the layer comprising carbon as a main component contains a hydrogen element of 1 atm% or more with respect to the carbon element.
- 11. (original): An electron-emitting device according to claim 10, wherein the layer comprising carbon as a main component contains a hydrogen element of 20 atm% or less with respect to the carbon element.
- 12. (currently amended): An electron-emitting device according to any one of claim[[s]] 1-to-11, wherein surface unevenness of the layer is smaller than 1/10 of its film thickness in rms.
- 13. (currently amended): An electron-emitting device according to any one of claim[[s]] 1 to 3.5, and 6, wherein the layer comprises carbon as a main component.
- 14. (currently amended): An electron-emitting device according to any one of claim[[s]] 4, 7, 8, and 13; wherein an average concentration of hydrogen with respect to carbon in the layer is 0.1 atm% or more.
- 15. (currently amended): An electron-emitting device according to any one of claim[[s]] 4, 7, 8, 9, and 13, wherein the layer comprising carbon as a main component has an sp<sup>3</sup> bonding.
- 16. (currently amended): An electron-emitting device according to any one of claim[[s]] 1-to 3, 5, and 9, wherein the particles comprise metal as a main component.

- 17. (currently amended): An electron-emitting device according to any one of claim[[s]] 6 to 8 and 16, wherein the metal is metal selected from Co, Ni, and Fe.
- 18. (currently amended): An electron-emitting device according to any one of claim[[s]] 1-to-3, 5, and 9, wherein the particles comprise monocrystalline metal as a main component.
- 19. (currently amended): An electron-emitting device according to any one of claim[[s]] 1-to-9, wherein the particles have an average particle diameter of 1 nm or more to 10 nm or less.
- 20. (currently amended): An electron-emitting device according to  $\frac{1}{2}$  or  $\frac{1}{2}$  of claim[[s]]  $\frac{1}{2}$  +  $\frac{1}{2}$ , wherein the layer has a thickness of 100 nm or less.
- 21. (currently amended): An electron-emitting device according to any one of claim[[s]] 1-to 4 and 7 to 9, wherein at least two adjacent particles among the plurality of particles are arranged 5 nm or less apart from each other.
- 22. (currently amended): An electron-emitting device according to any one of claim[[s]] 4-to-9, wherein a density of the particles in the layer is  $1 \times 10^{14}$ /cm<sup>3</sup> or more and  $5 \times 10^{18}$ /cm<sup>3</sup> or less.
- 23. (currently amended): An electron-emitting device according to  $\frac{1}{2}$  or or of claim[[s]] 1 + o 9, wherein a density of the particles in the layer is  $1 \times 10^{15}$ /cm<sup>3</sup> or more and  $5 \times 10^{17}$ /cm<sup>3</sup> or less

- 24. (currently amended): An electron-emitting device according to any-one of claim[[s]] 4-to-9, wherein a concentration of a main element of the particles with respect to a main element of the layer is 0.001 atm% or more and 1.5 atm% or less.
- 25. (currently amended): An electron-emitting device according to any one of claim[[s]] 1-to-9, wherein a concentration of a main element of the particles with respect to a main element of the layer is 0.05 atm% or more and 1 atm% or less.
- 26. (currently amended): An electron-emitting device according to <del>any one</del> of claim[[s]] 1-to 3 and 9, wherein:

the plurality of particles are arranged dispersedly in the layer as a plurality of groups of particles, each group being constituted by at least two adjacent particles[[:]], one of the two adjacent particles are placed to be nearer to the cathode

electrode than the other particle[[;]], and

the plurality of groups of particles are arranged apart from each other by  $\underline{a}$  distance equal to an average film thickness of the layer or more.

- 27. (currently amended): An electron-emitting device according to any one of claim[[s]] 1-to-26, wherein the surface of the layer is terminated with hydrogen.
- 28. (currently amended): An electron-emitting device according to <del>any one</del> of claim[[s]] 1+<del>o 27</del>, further comprising:
- an insulating film which is arranged on the cathode electrode and has a first opening; and

a gate electrode which is arranged on the insulting film and has a second opening, wherein[[:]]

the first opening and the second opening communicate with each other [[:]], and

the layer is exposed in the first opening.

- (currently amended): An electron source, wherein a plurality of the electron-emitting devices according to any one of claim[[s]] 1-to-28 are arranged.
- 30. (original): An image display apparatus, characterized by comprising the electron source according to claim 29 and a light-emitting member which emits light by being irradiated with electrons.

31. - 40. (canceled).

- 41. (new): An electron-emitting device comprising:
- a cathode electrode; and
- a layer electrically disposed on the cathode electrode, wherein
- a plurality of particle groups comprising at least two adjacent particles are discretely distributed in the layer.

the particle comprises as a main component a material which has resistivity lower than resistivity of a material of the layer,

one of the adjacent particles is closer to the cathode electrode rather than the other(s) of the adjacent particles, and

the adjacent particles are disposed within a distance of 5nm.

- 42. (new): An electron-emitting device according to claim 41, wherein the layer comprises carbon as a main component.
- 43. (new): An electron-emitting device according to claim 42, wherein the layer contains hydrogen.
- 44. (new): An image display apparatus comprising a plurality of electronemitting devices and a light emitting member emitting light by irradiation with an electron emitted from the electron-emitting device, wherein the each of the electron-emitting devices is the electron-emitting devices according to claim 41.
  - 45. (new): An electron-emitting device comprising:
  - a cathode electrode:
- a layer electrically connected to the cathode electrode containing carbon as a main component; and
- a plurality of particles arranged in the layer containing carbon as a main component, wherein
- the layer containing carbon as a main component contains hydrogen of 0.1- 20 atm% at a ratio to the carbon.
- 46. (new): An image display apparatus comprising a plurality of electronemitting devices and a light emitting member emitting light by irradiation with an electron emitted from the electron-emitting device, wherein each of the electron-emitting devices is an electron-emitting device according to claim 45.